

## Silicon NPN Power Transistors

2SC3568

## DESCRIPTION

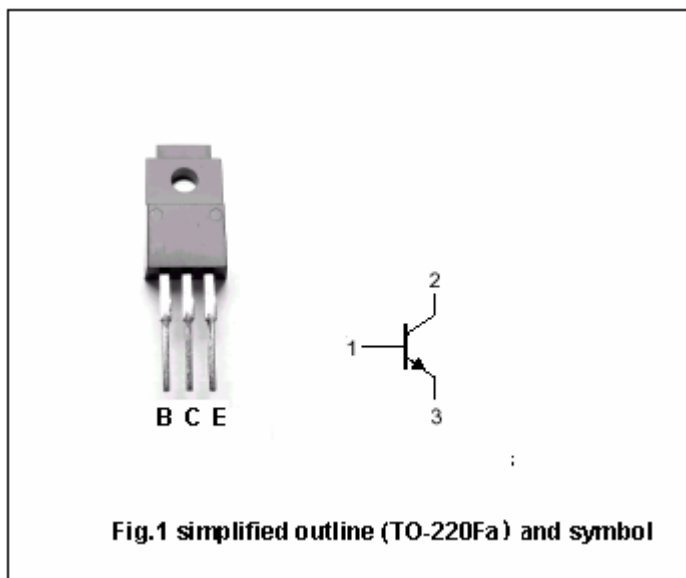
- With TO-220Fa package
- Complement to type 2SA1396
- Low collector saturation voltage
- High switching speed

## APPLICATIONS

- Switching regulator
- DC-DC converter
- High frequency power amplifier

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	150	V
$V_{CEO}$	Collector-emitter voltage	Open base	100	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current(DC)		10	A
$I_{CM}$	Collector current-peak		20	A
$I_B$	Base current (DC)		5	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	30	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A; L=1mH	100			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A			0.6	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			10	μA
I <sub>CEX</sub>	Collector cut-off current	V <sub>CE</sub> =100V; V <sub>BE(OFF)</sub> =-1.5V T <sub>a</sub> =125°C			10 1.0	μA mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =5V	40			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =5V	40		200	
h <sub>FE-3</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	20			

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =5A ; I <sub>B1</sub> =-I <sub>B2</sub> =0.5A V <sub>CC</sub> ≈50V; R <sub>L</sub> =10Ω			0.5	μs
t <sub>s</sub>	Storage time				1.5	μs
t <sub>f</sub>	Fall time				0.5	μs

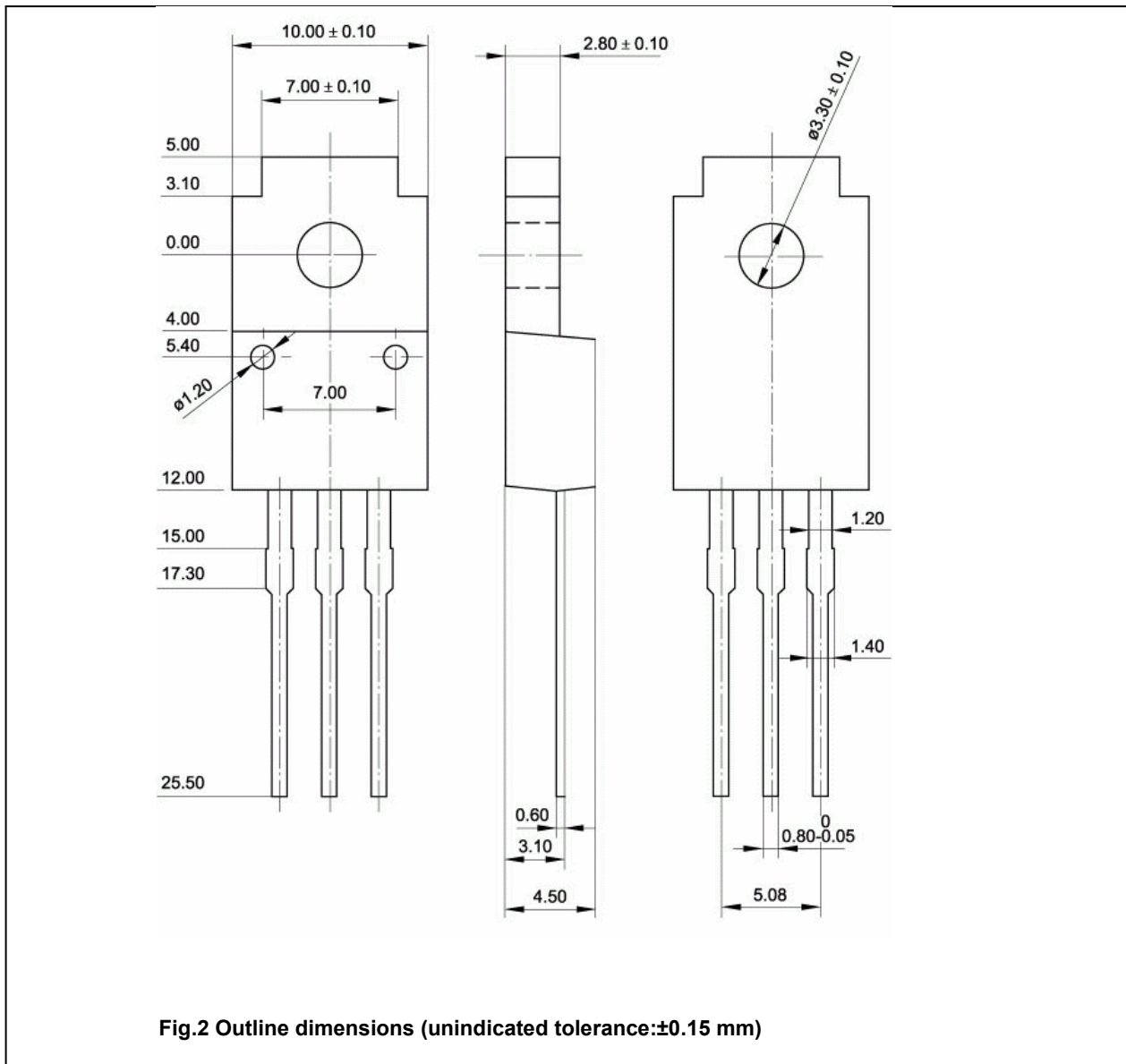
◆ h<sub>FE-2</sub> Classifications

M	L	K
40-80	60-120	100-200

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PACKAGE OUTLINE



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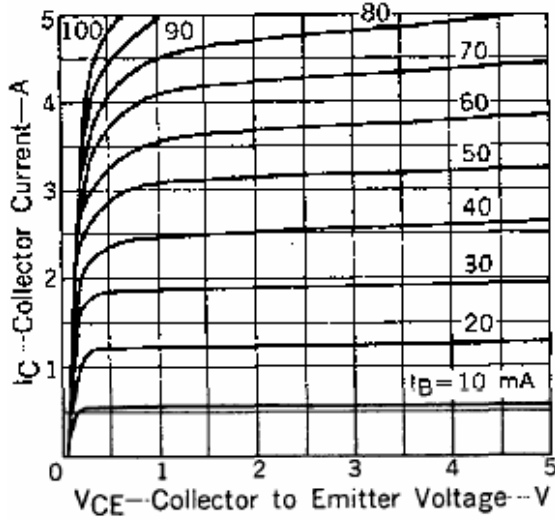


Fig.3 Static Characteristic

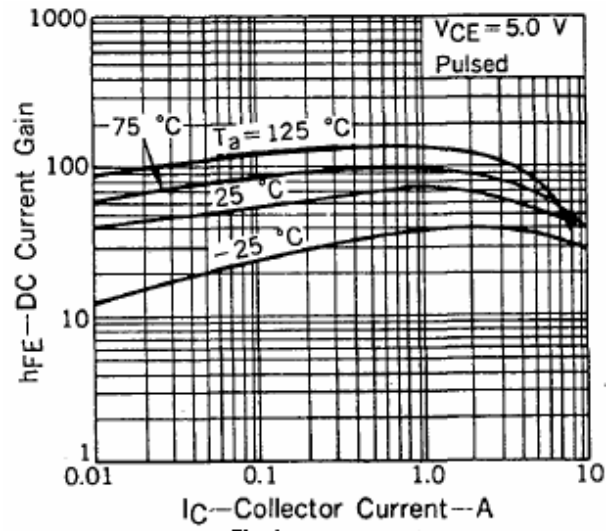


Fig.4 DC current Gain

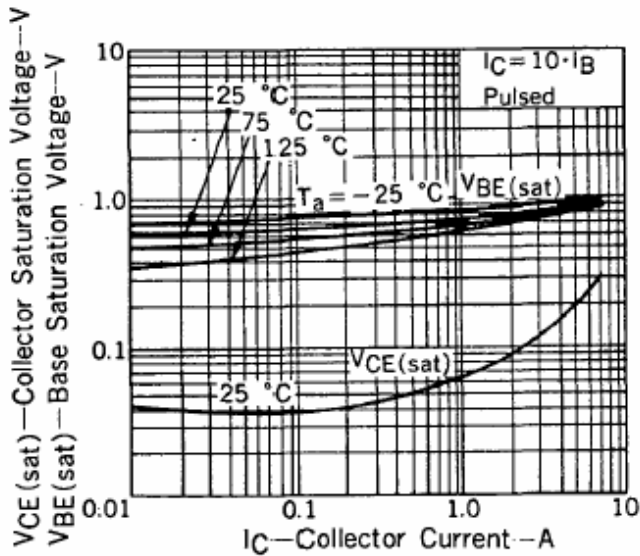


Fig.5 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

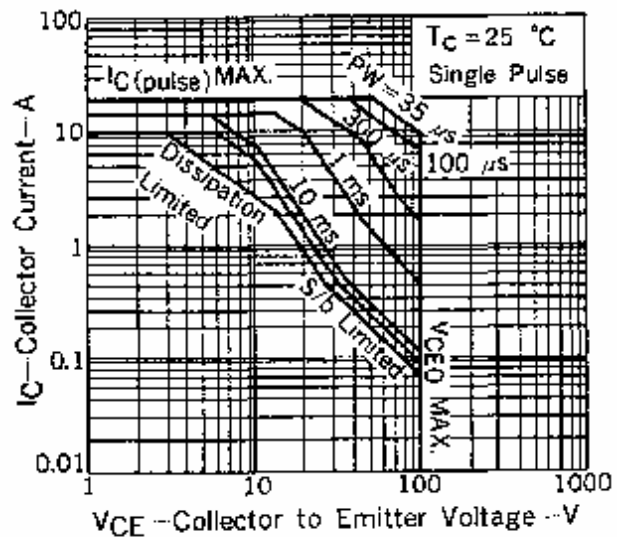


Fig.6 Safe Operating Area